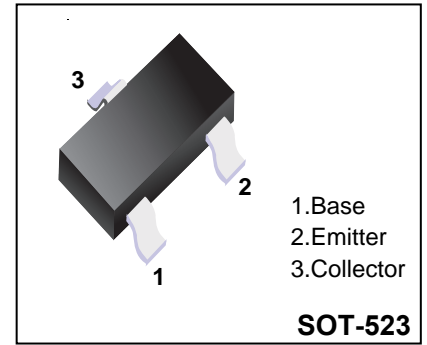


**TRANSISTOR (NPN)**

**FEATURES**

- ◆ Complimentary to S8550
- ◆ Collector Current:  $I_C=0.5A$

**MARKING:J3Y**



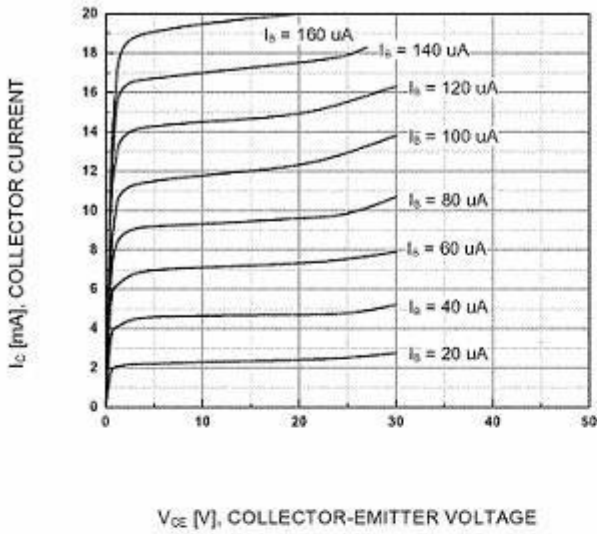
**MAXIMUM RATINGS (TA=25°C unless otherwise noted)**

Parameter	Symbol	Value	Units
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current -Continuous	$I_C$	0.5	A
Collector Dissipation	$P_C$	0.3	W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55-150	°C

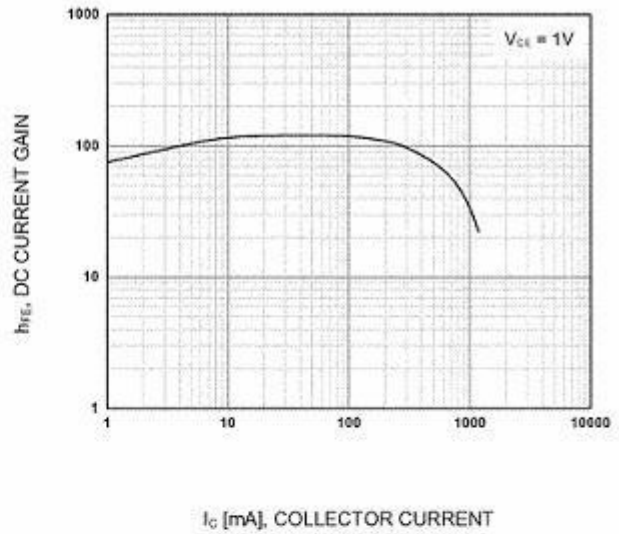
**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40V, I_E=0$			0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CB}=20V, I_E=0$			0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			0.1	$\mu A$
DC current gain	$H_{FE(1)}$	$V_{CE}=1V, I_C=50mA$	200		350	
	$H_{FE(2)}$	$V_{CE}=1V, I_C=500mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=50mA$			1.2	V
Transition frequency	$f_T$	$V_{CE}=6V, I_C=20mA$ $f=30MHz$	150			MHz

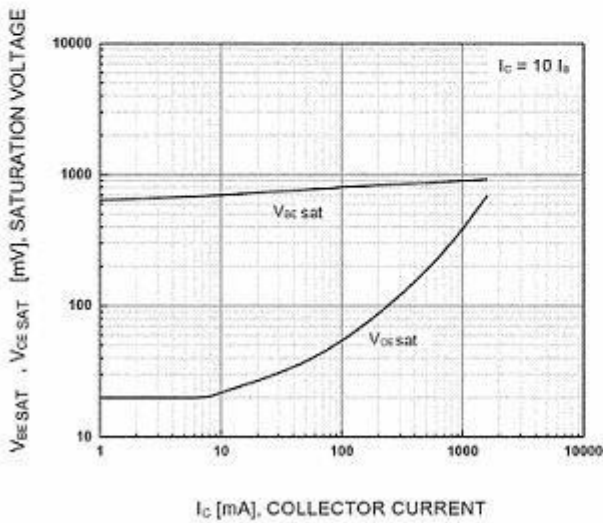
Typical Characteristics



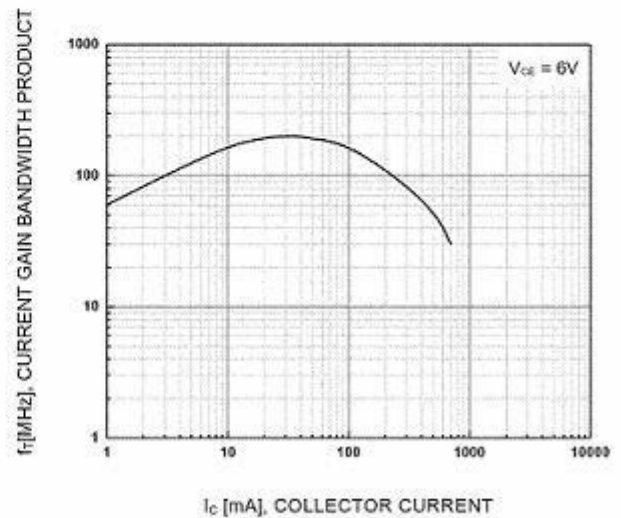
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

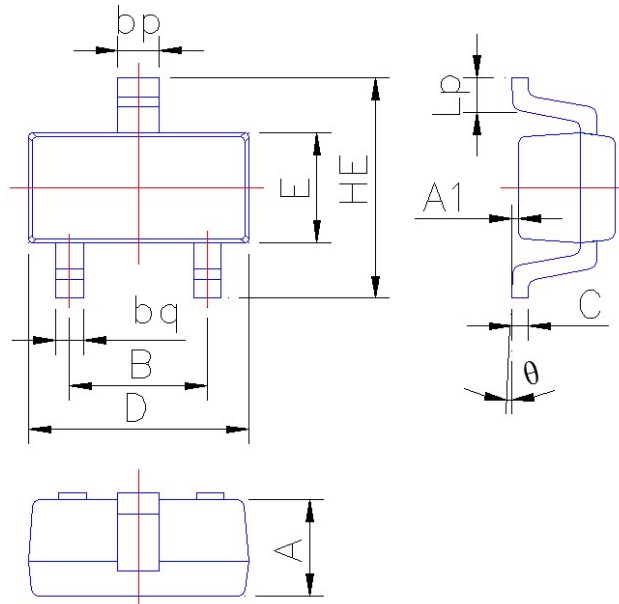


Current Gain Bandwidth Product

**Package Outline**

**SOT-523**

Plastic surface mounted package; 3 leads



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.80
A1	0.010	0.100
B	0.95	1.05
bp	0.26	0.40
bq	0.16	0.30
C	0.09	0.15
D	1.50	1.70
E	0.70	0.85
HE	1.45	1.75
Lp	0.16	0.36
θ	0°	5°

**Summary of Packing Options**

Package	Packing Description	Packing Quantity	Industry Standard
SOT-523	Tape/Reel,7"reel	3000	EIA-481-1